

F. Silicon Device and Integration Technology 분과

Room G

하나스퀘어 (B112)

일 시 : 2월 16일(목) 09:30-11:00

세션명 : [TG1-F] Device Technology for Advanced Materials and Devices

좌 장 : 양지운(고려대학교), 이충호(삼성전자)

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| TG1-F-1 | 09:30-09:45 | Investigation of Logic Circuit with Vertical Type Single-electron Transistor
저자: Kyung-Wan Kim, Jung Han Lee, Kwon-Chil Kang, and Byung-Gook Park
소속: Inter-University Semiconductor Research Center (ISRC), and School of Electrical Engineering and Computer Science, Seoul National University |
| TG1-F-2 | 09:45-10:00 | Study of PMOS Poly Depletion Effect at Metal/Poly-SiGe Gate
저자: 김태윤, 조흥재, 백건훈, 황의성, 김춘환, 홍권, 강효상
소속: Memory R&D Division, Hynix Semiconductor Inc. |
| TG1-F-3 | 10:00-10:15 | A 600 V Trench Gate MOSFET with Charge Sheet Super Junction (CSSJ)
저자: 백상원 ¹ , 조동환 ¹ , 최보식 ² , 이호준 ¹ , 이준영 ¹ , 박현진 ² , 이정수 ^{1,2}
소속: ¹ Pohang University of Science and Technology 전자전기공학과, ² Pohang University of Science and Technology 정보전자융합공학부 |
| TG1-F-4 | 10:15-10:30 | A Fully Digital On-chip Process Variation Sensor using Time-to-digital Converter
저자: 오름 ¹ , 성만영 ²
소속: ¹ 삼성전자 DRAM 설계팀, ² 고려대학교 전기전자전파공학과 |
| TG1-F-5 | 10:30-10:45 | A Simple and accurate Modeling of Non-rectilinear Gate Shape with Trapezoidal Approximation
저자: M. H. Ryu and Y. M. Kim
소속: School of Electrical and Computer Engineering, UNIST |